



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): S. UNO, et al

Serial No.:

09/646,671

Filed:

September 20, 2000

For:

MANUFACTURING METHOD OF SEMICONDUCTOR

INTEGRATED CIRCUIT DEVICE AND SEMICONDUCTOR

INTEGRATED CIRCUIT DEVICE

Group:

Examiner:

PROPOSED AMENDMENT TO THE DRAWINGS

Commissioner for Patents Washington, D.C. 20231

April 5, 2001

Sir:

It is proposed that the drawings in the above-identified application be amended in accordance with the attached redlined print, and approval of these drawing corrections is respectfully requested at this time.

Upon receipt of the approval of the amendment to the drawings and receipt of the official Notice of Allowance, the drawing amendments will be effected in accordance with the new procedures set forth in 1017 OG 4.

Respectfully submitted

William I. Solomon

Registration Nó. 28,565

ANTONELLI, TERRY, STOUT & KRAUS, LLP

WIS/DRA/cee Attachment(s) (703) 312-6600

EIG_1

FIG. 1(b)

$$F = Si - F \quad C = O$$

$$F = SiO_2$$

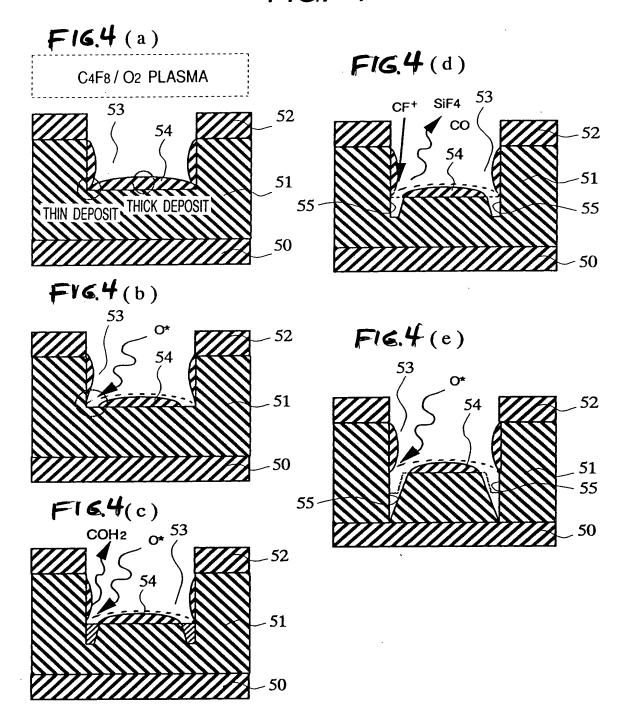
METASTABLE STRUCTURE

$$\begin{array}{c} \mathsf{DECOMPO}\text{-}\\ \mathsf{SITION} \end{array} \rightarrow \begin{array}{c} \mathsf{VAPOR}\text{-}\\ \mathsf{IZATION} \end{array}$$

FIG. 3(a)

F16. 3(1)

F16. 3(c)



EIG. 5

REPULSION
$$2eV$$

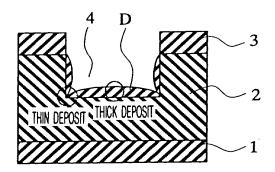
N*

O—Si—CH3

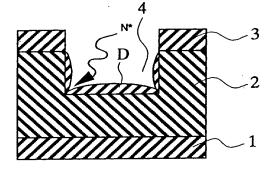
STABILIZATION



F16.6(a)

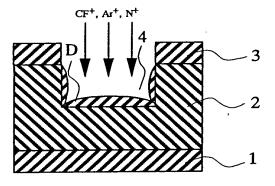


F16.6(b)

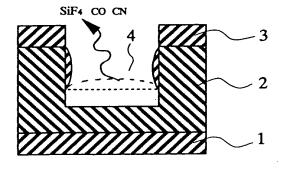


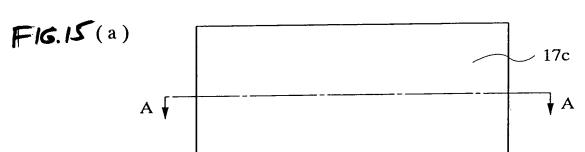
- 1: INSULATING FILM
- 2: ORGANIC INSULATING FILM
- 3: PHOTORESIST FILM
- 4: RECESS

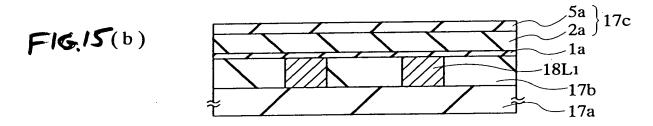
F16.6(c)



F16.6(d)







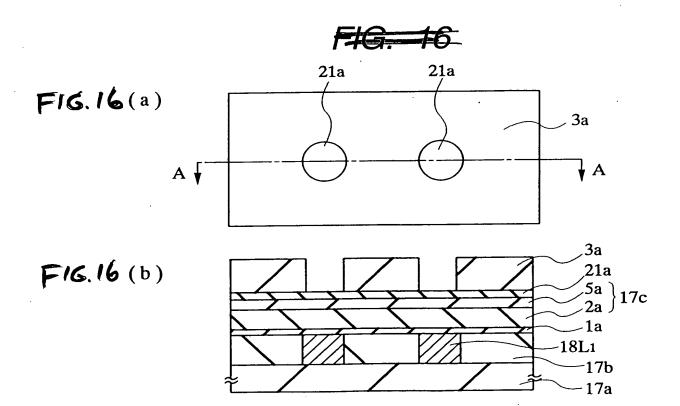


FIG. 17(a) 4b1 1a 4b1 1a 3a A FIG. 17(b) 3a 21a 5a 21a 5a 21a 18L1 17b 17a

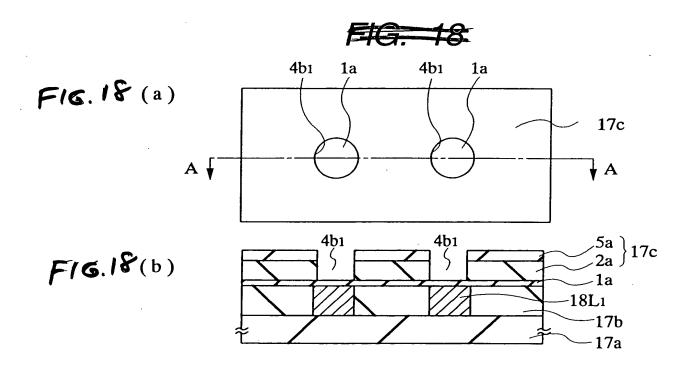
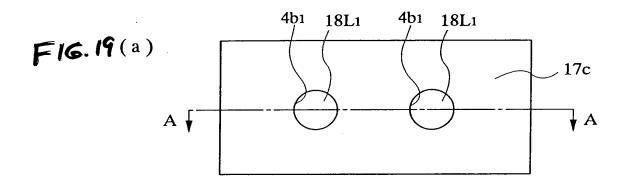
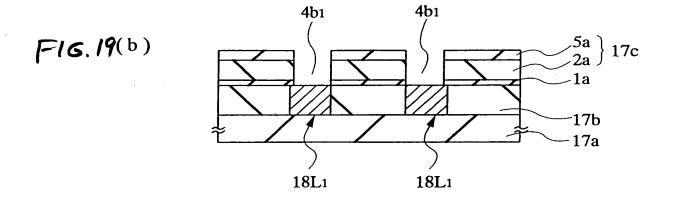
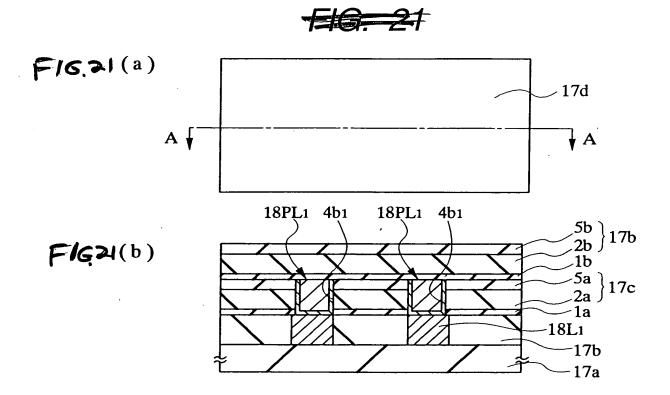


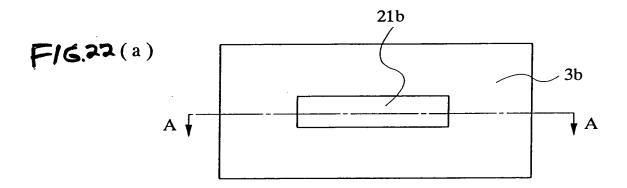
FIG. 19

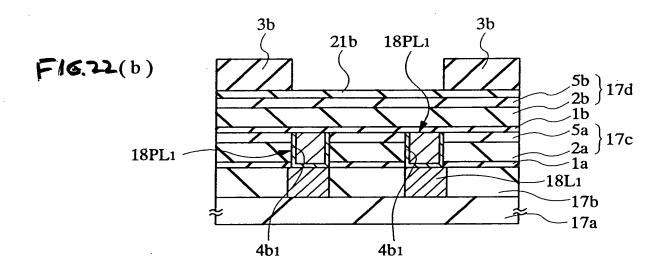




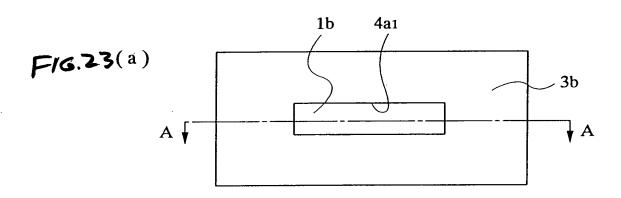
##C. 20 4b1 18PL1 4b1 18PL1 A 4b1 18PL1 4b1 18PL1 4b1 18PL1 4b1 18PL1 5a 2a 17c 17b 17a

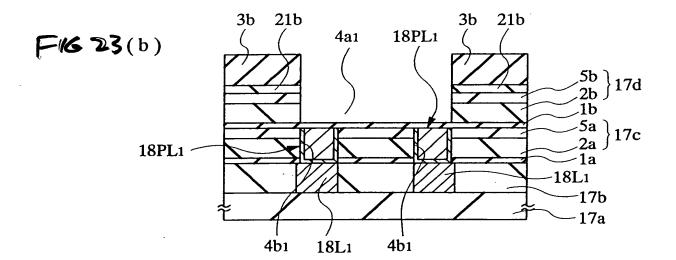




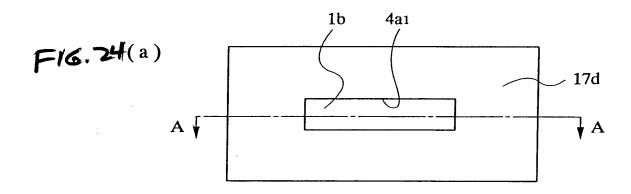


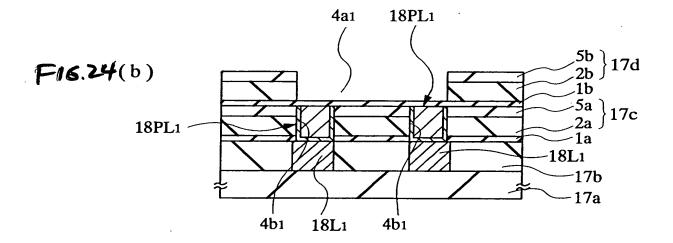
20 / 85

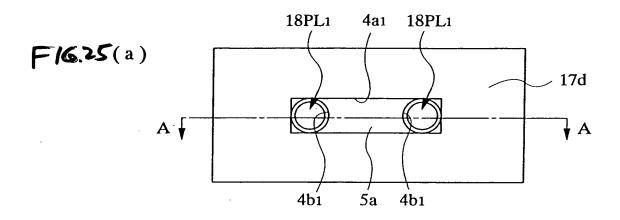


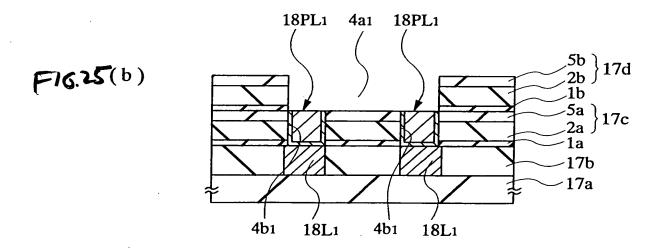


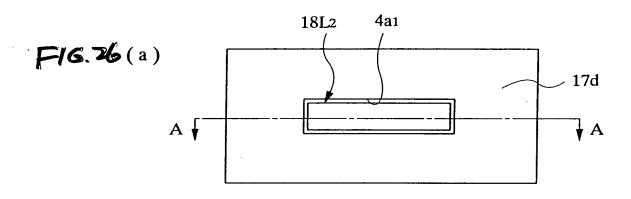
F10. 24

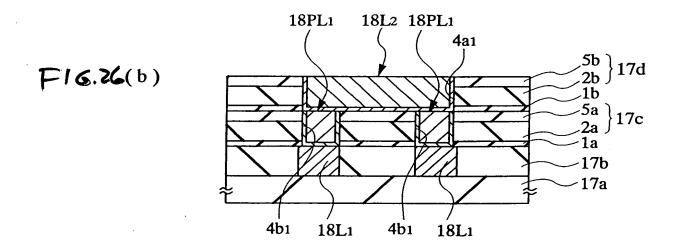


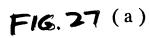


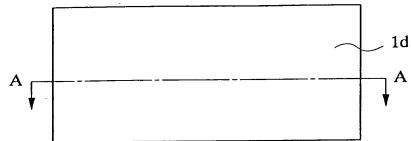




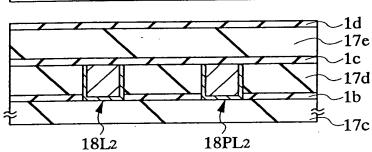




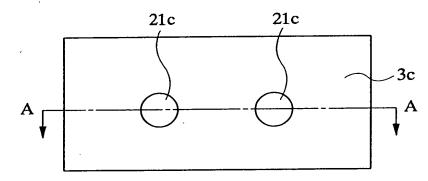




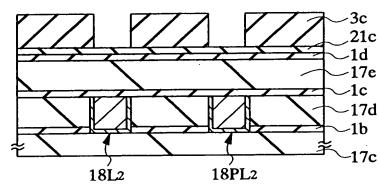
F16.27(b)

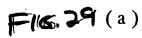


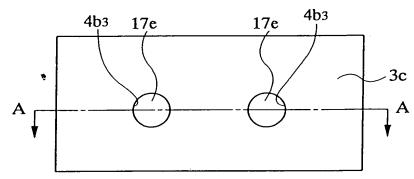
F16.28 (a)



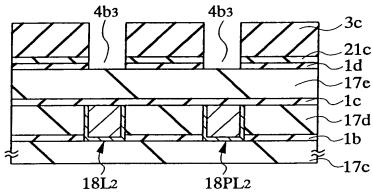
F16.28(b)



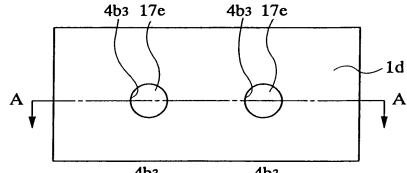




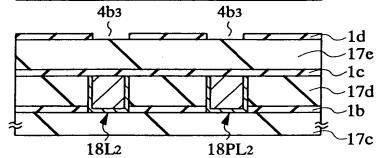
F16.29(b)

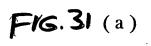


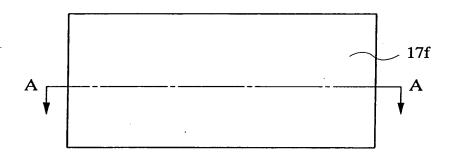
F16.30(a)



F16.30(b)







F16.31(b)

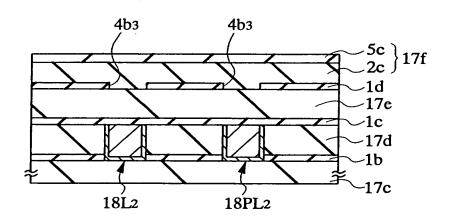
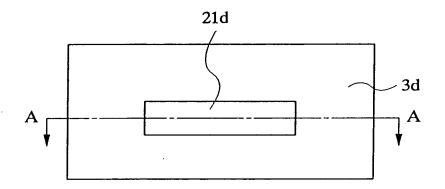
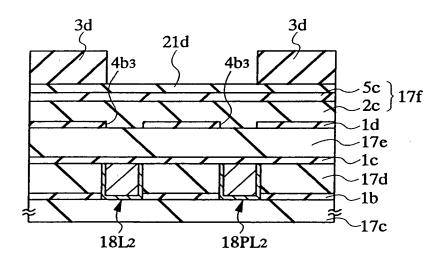


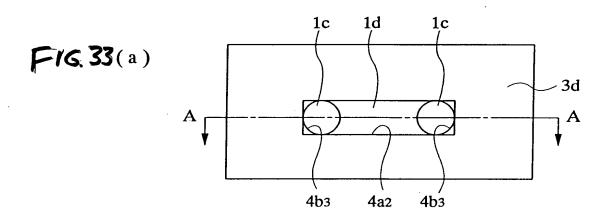
FIG: 32

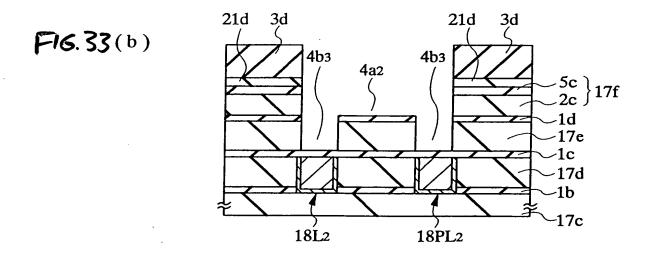


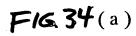


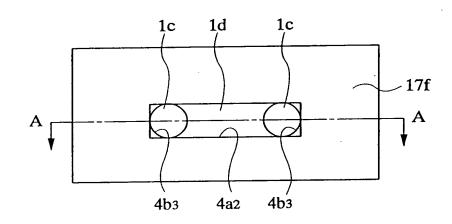
F16.32(b)



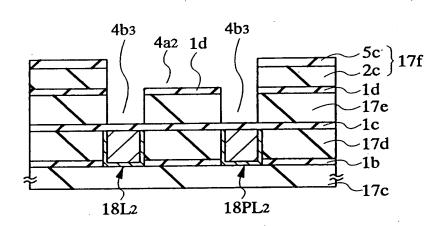




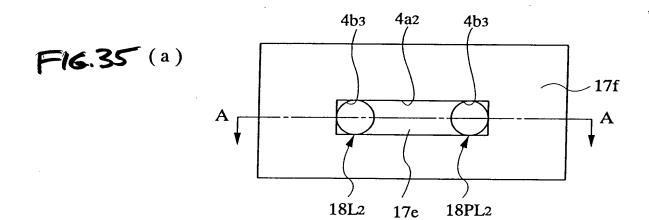


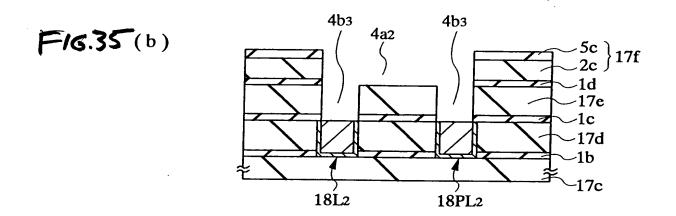


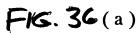
F16.34(b)

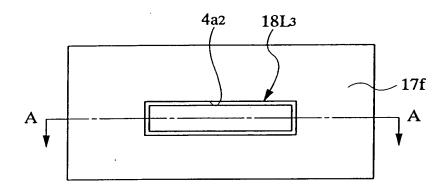


EIG 35

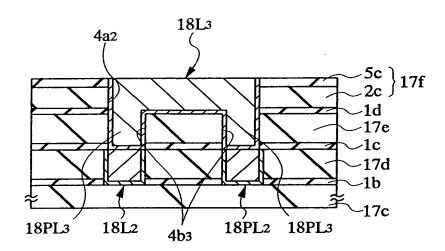


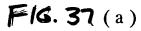


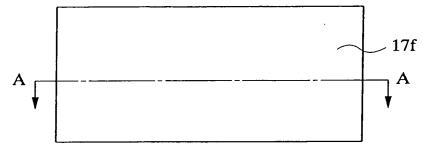




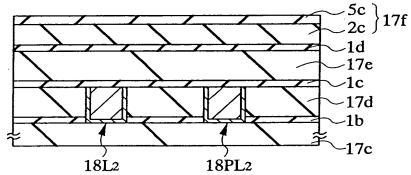
F16.36(b)



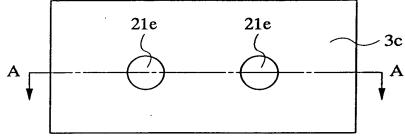




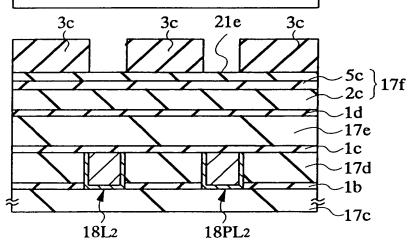
F16.37 (b)



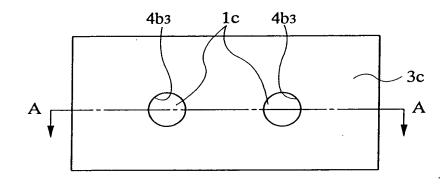
F16.38 (a)



F16.38_(b)



F16. 39 (a)



F16.39(b)

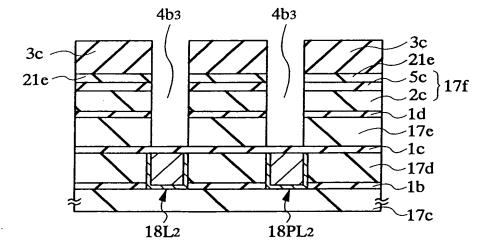


FIG. 40(a)

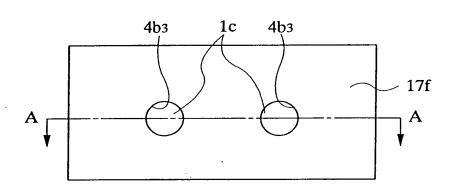
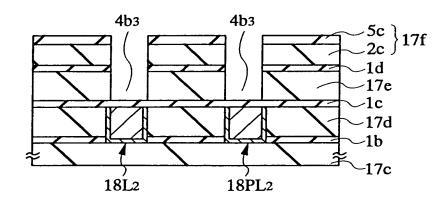
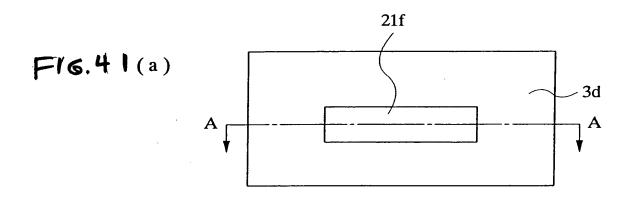


FIG. 40(b)





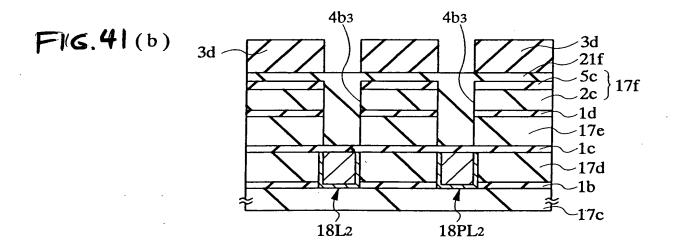
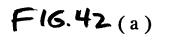
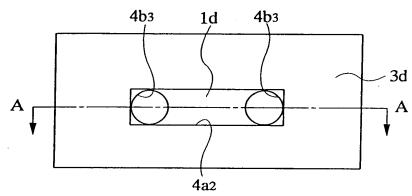
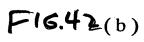
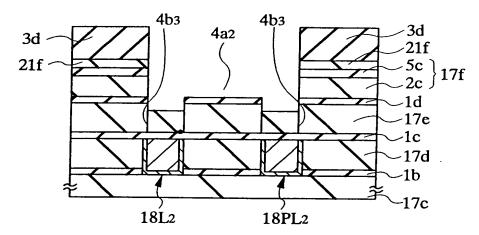


FIG: 42

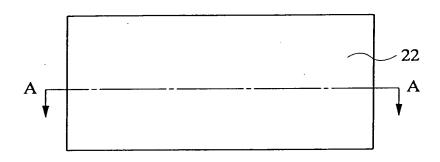




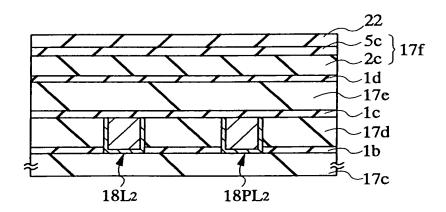


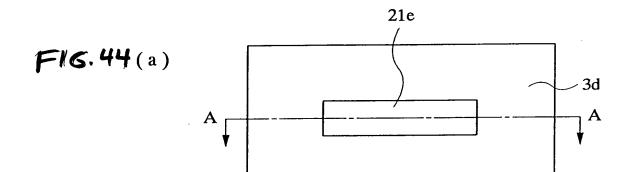


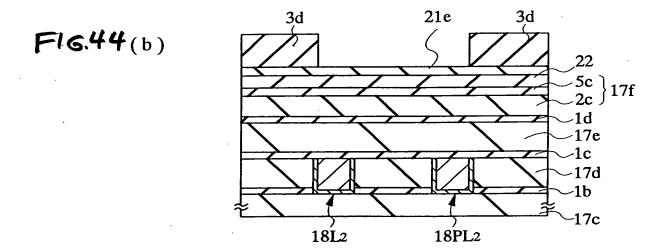
F16.43 (a)



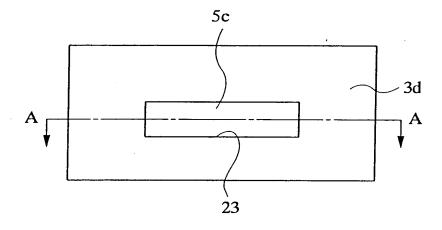
F16.43(b)



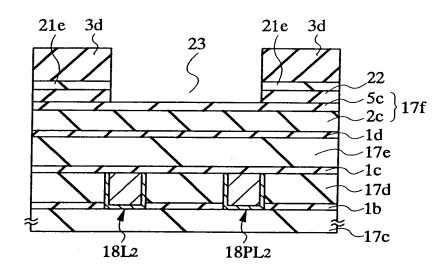


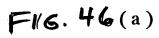


F16.45 (a)



F16.45(b)





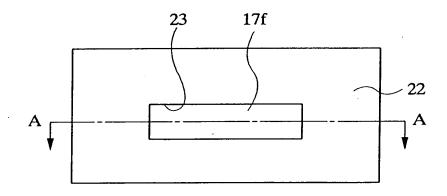
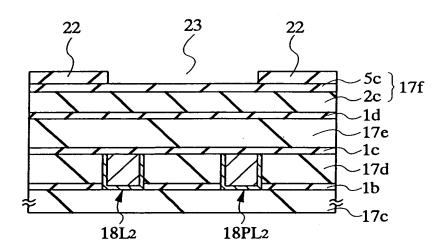
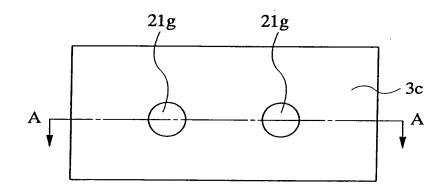


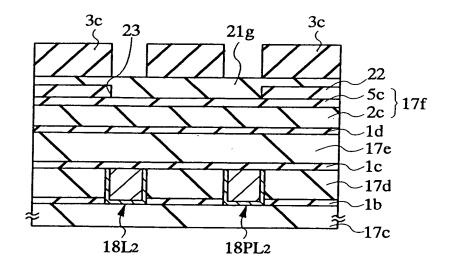
FIG. 46(b)



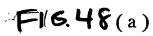
F16.47 (a)

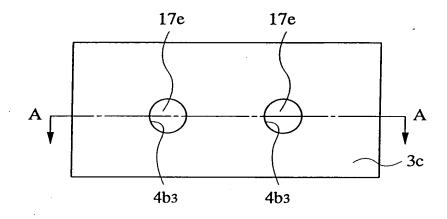


F16.47(b)

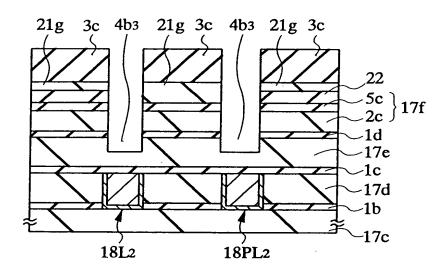


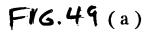
EIG. 48.

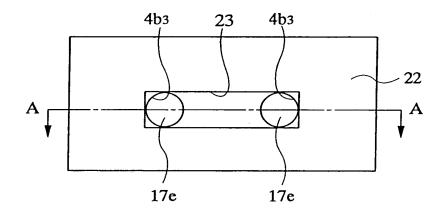


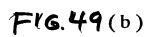


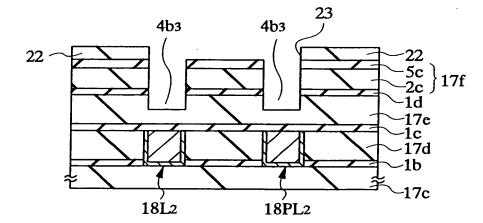
F16.48(b)



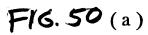


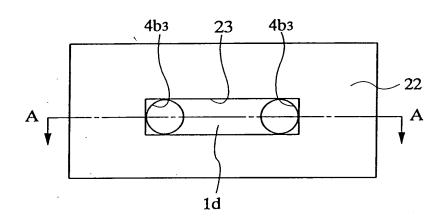




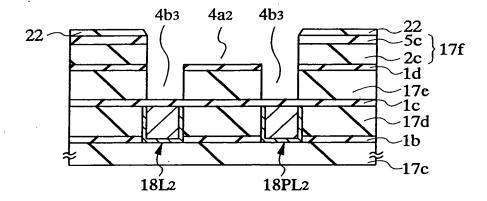


EIG. 50

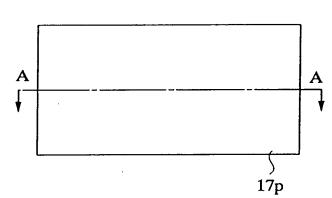




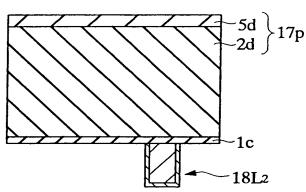
F16.50(b)



F16.51 (a)

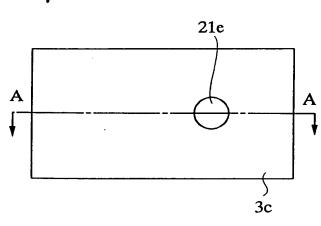


F16.51 (b)

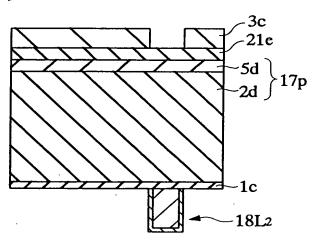


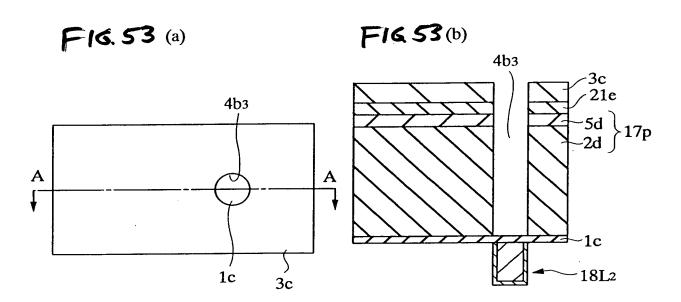
EIG. 52

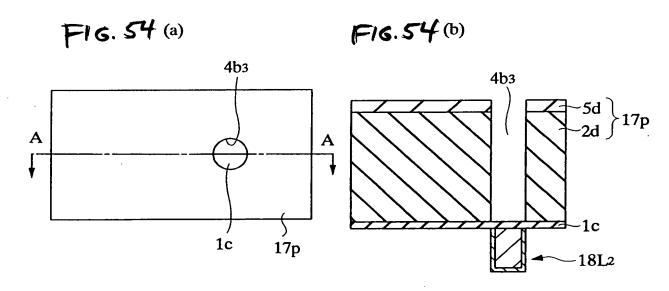
F16.52 (a)



F16.52(b)







EIG. 55

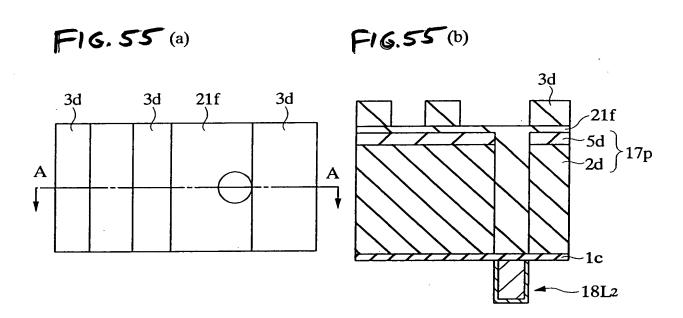


FIG. 56 (a)

FIG.56 (b)

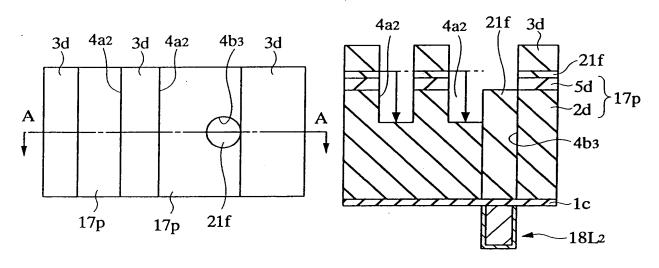
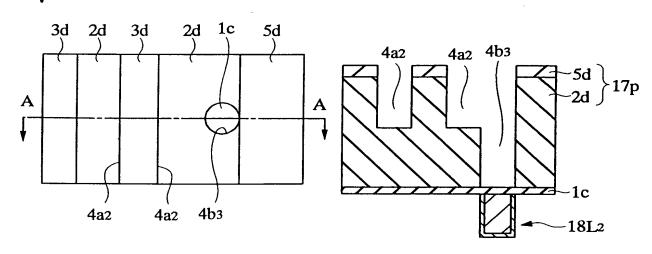


FIG. 57

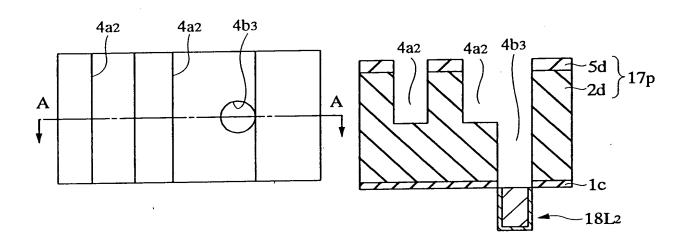
F16.57 (a)

FIG. 57(b)



F16.58 (a)

F16.58(b)



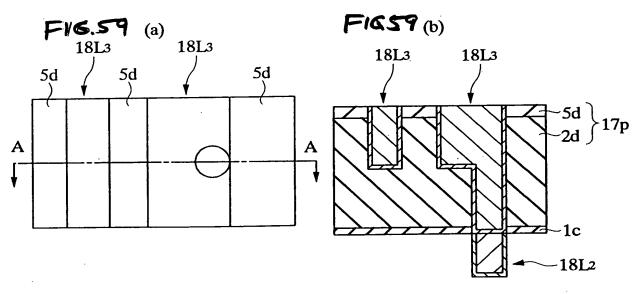
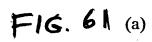
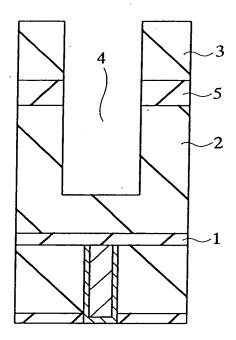


FIG. 61





F16.61 (b)

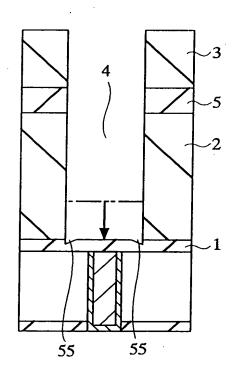
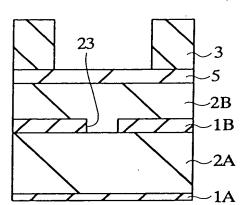
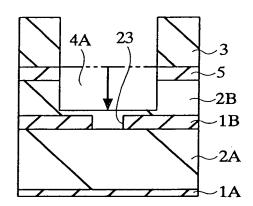


FIG. 62

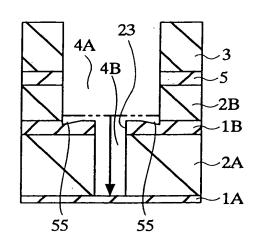
F1662(a)

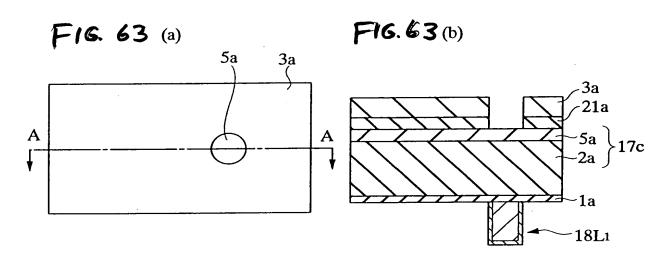


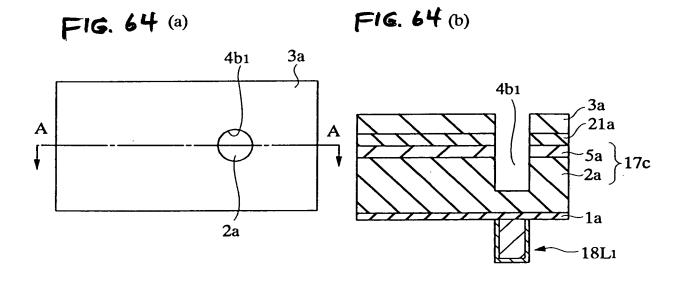
F16.62 (b)

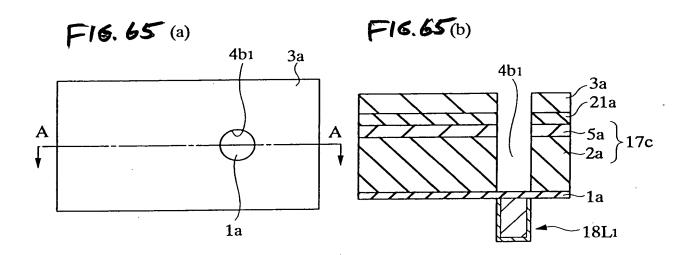


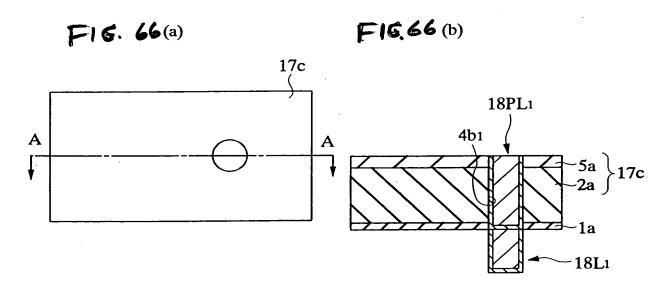
F16.62 (c)

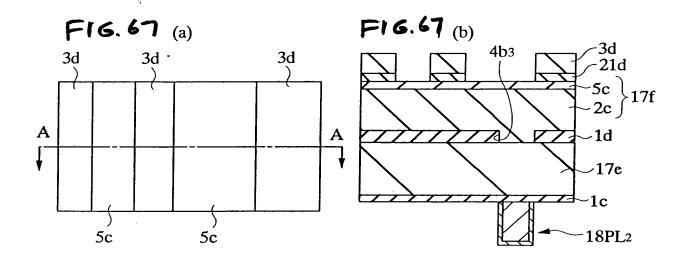


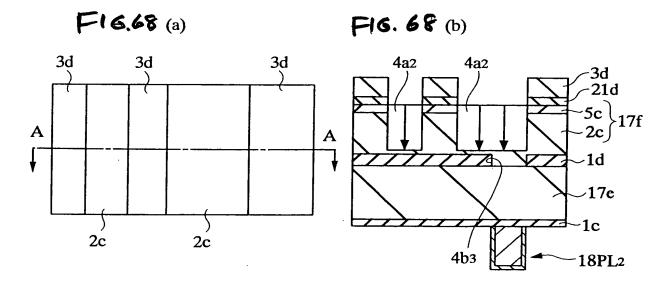


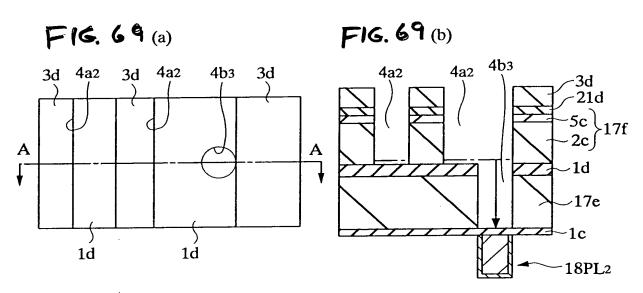


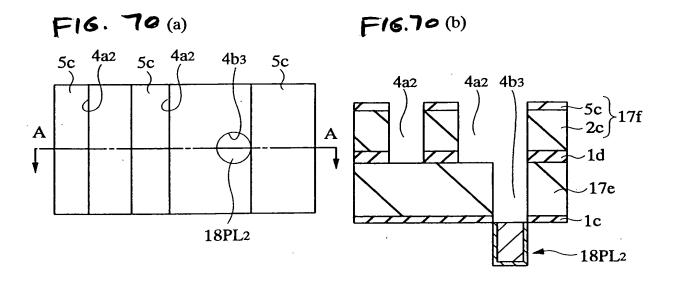




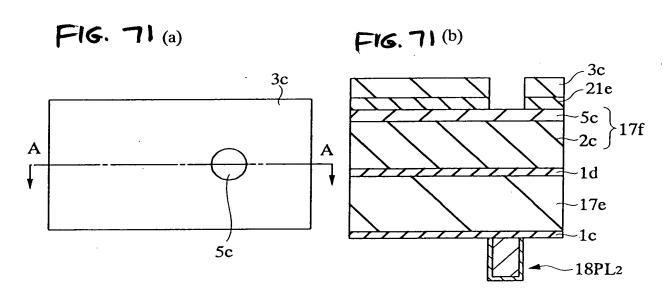


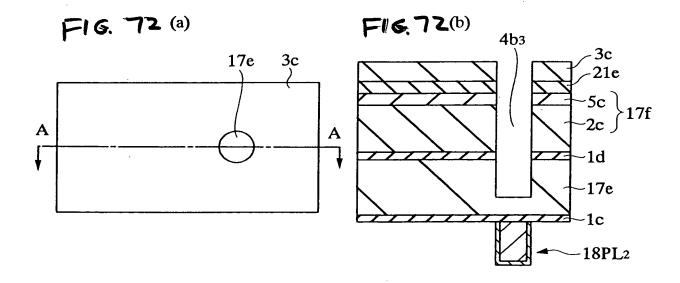


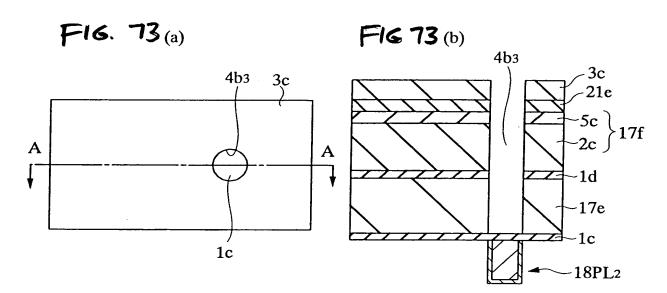


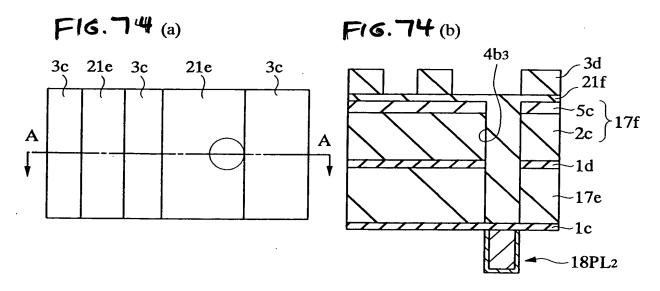


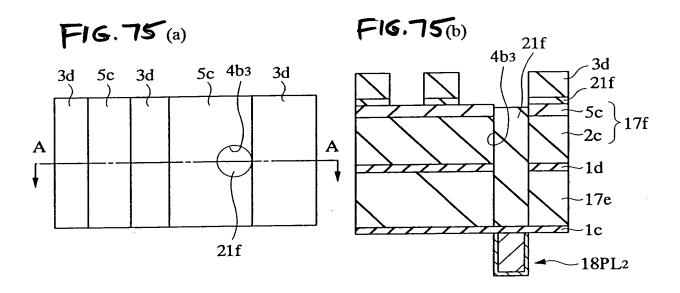
EIG. 79

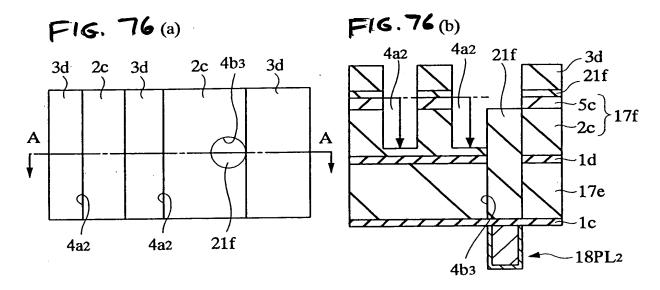


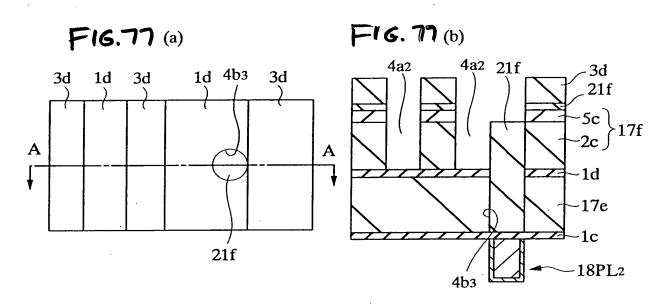


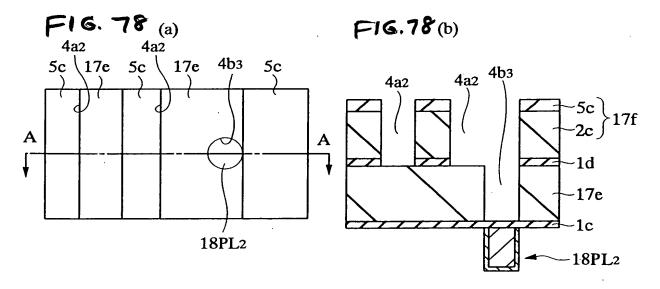


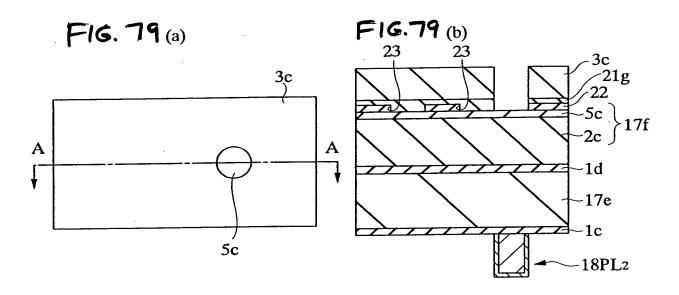


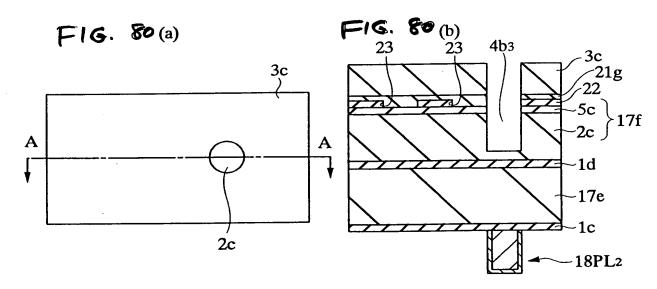












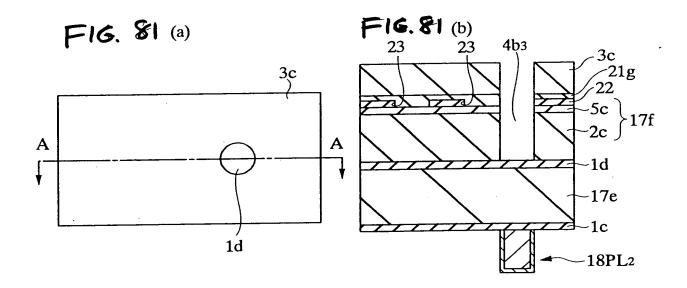
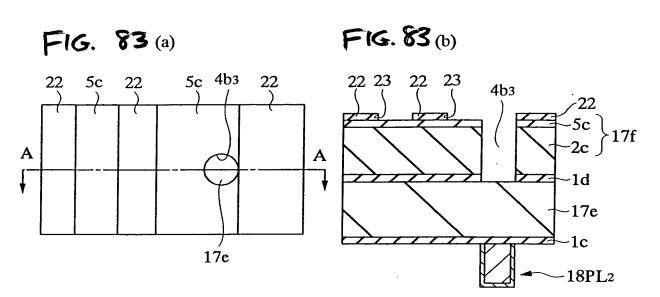
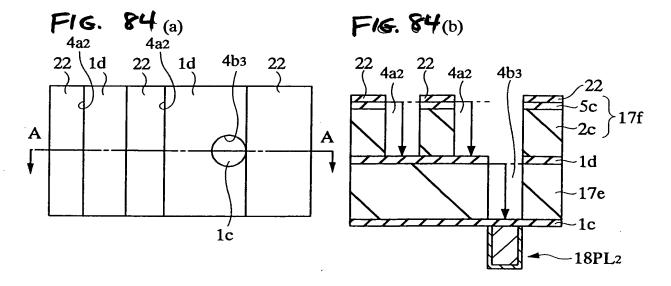
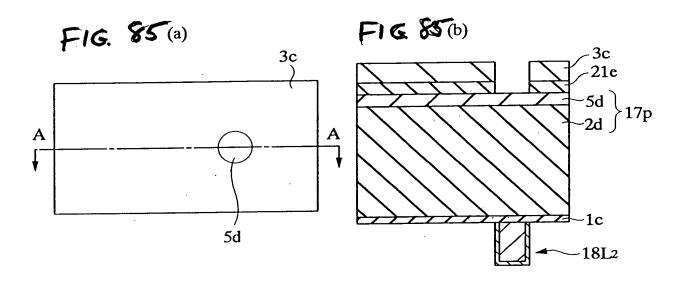
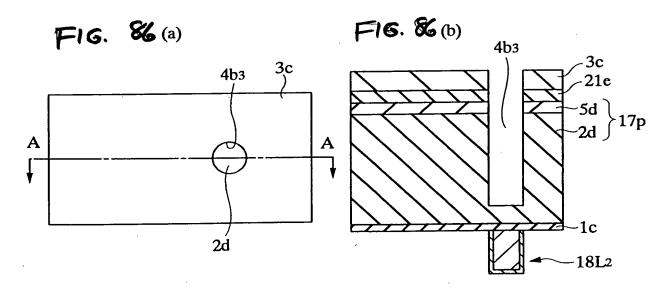


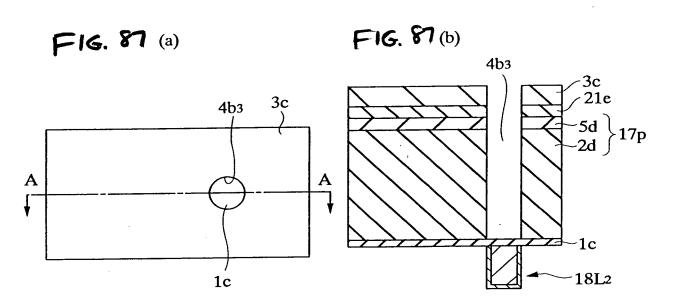
FIG. 82 (a) FIG. 82 (b) 23 23 4b3 3c 21g 22c 5cc 17f 1d 17e 18PL2











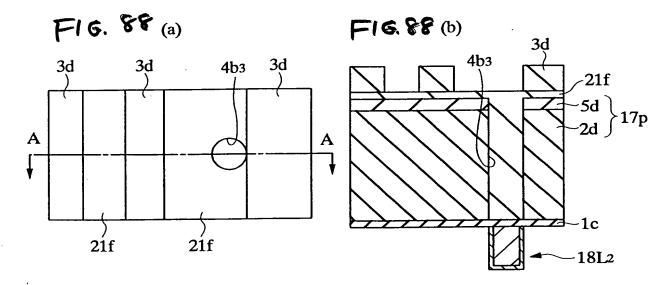
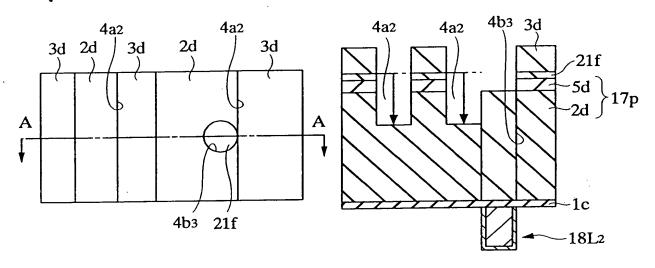
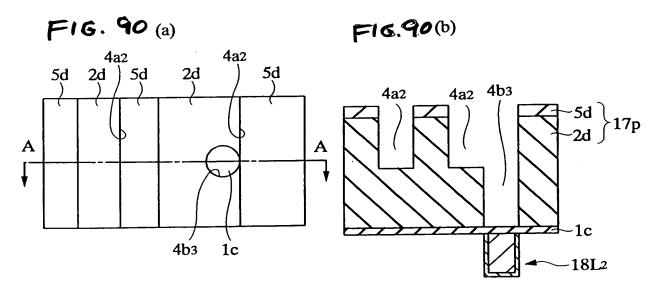
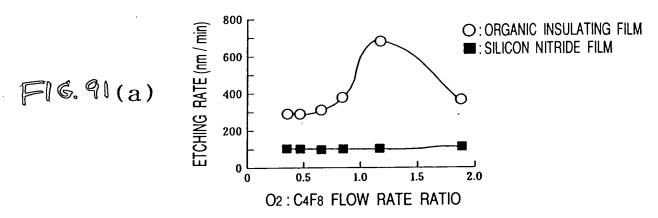


FIG. 89 (a)

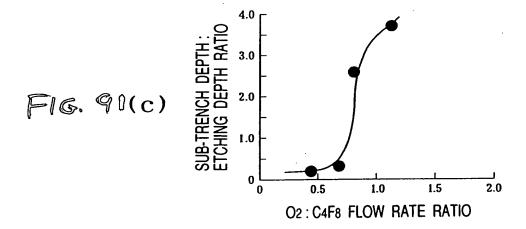
FIG. 89 (b)







O2:C4F8 FLOW RATE RATIO	0.2	0.4	0.6	0.8	1.5
ETCHING FORM	4 TAPER ANGLE	4 ORGANI LATING	4 C INSU- FILM	4	4



EIG-92

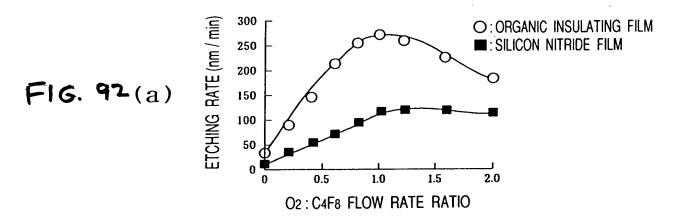
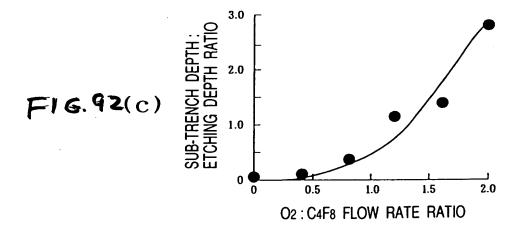
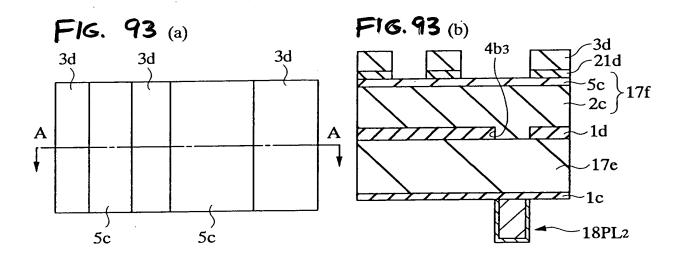
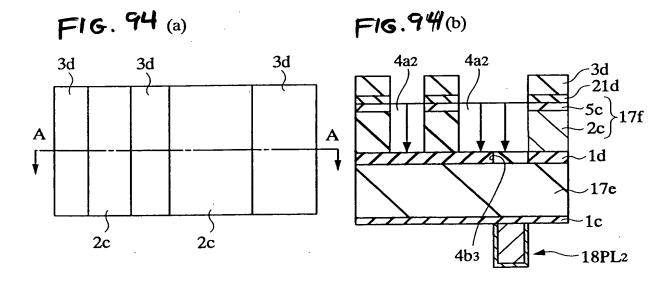


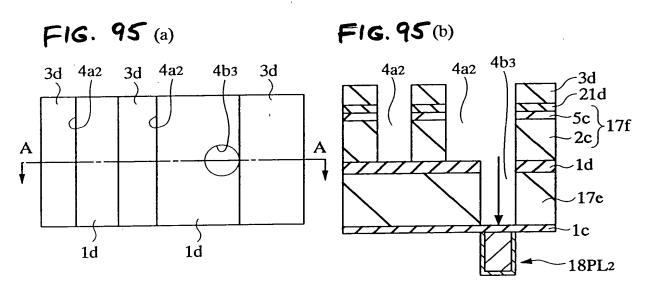
FIG. 92(b)

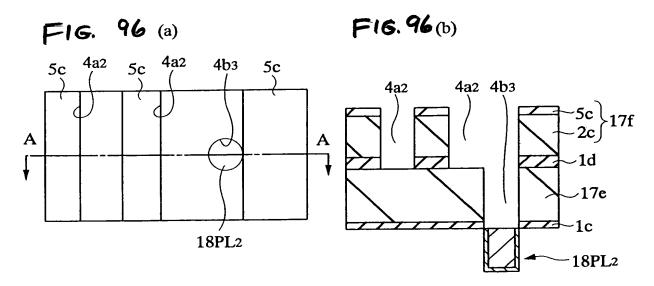
	O2:C4F8 FLOW RATE RATIO	0	0.5	1.0	1.5	2.0
(D)	ETCHING FORM	TAPER ANGLE	ORGANIC LATING	C INSU- FILM		

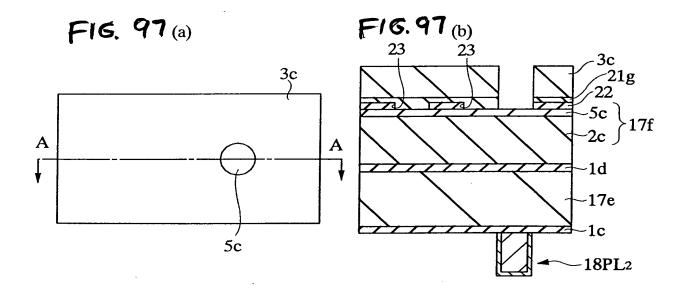


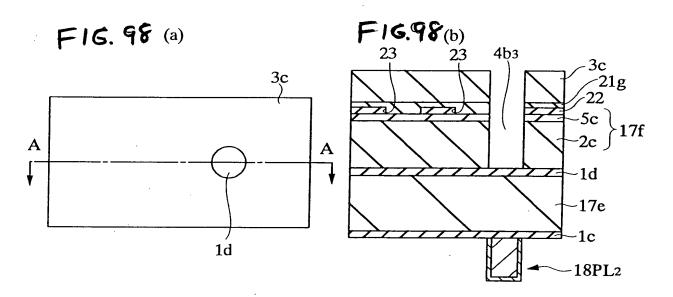












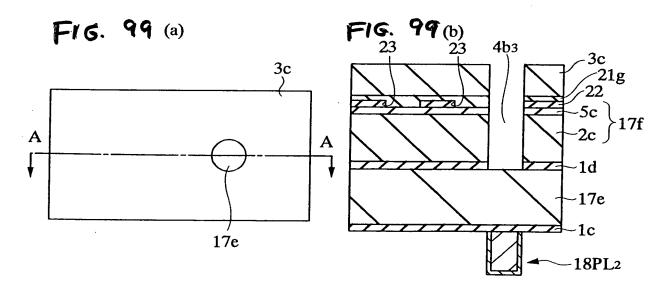
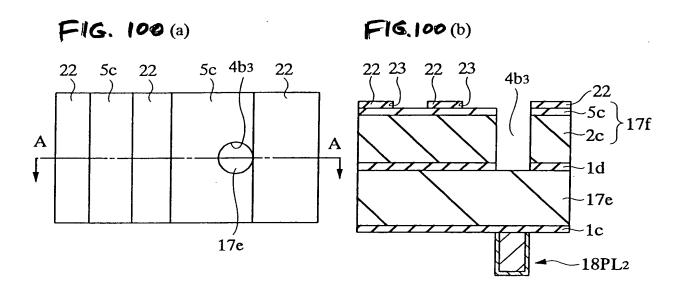


FIG. 100-



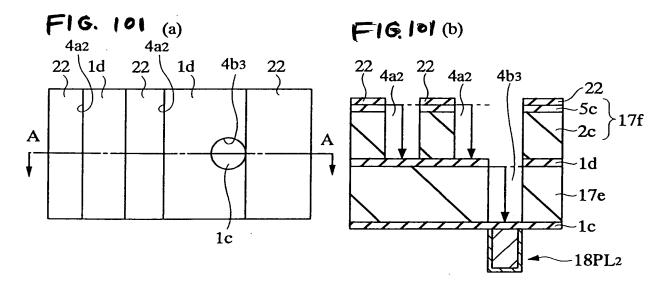


FIG. 103(a)

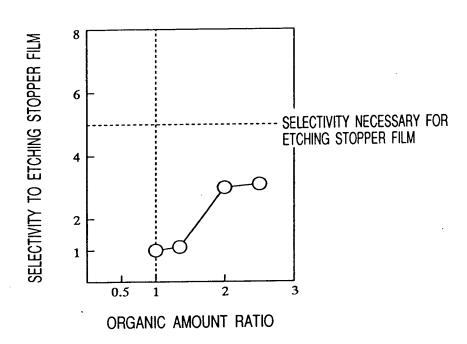


FIG. 103(b)

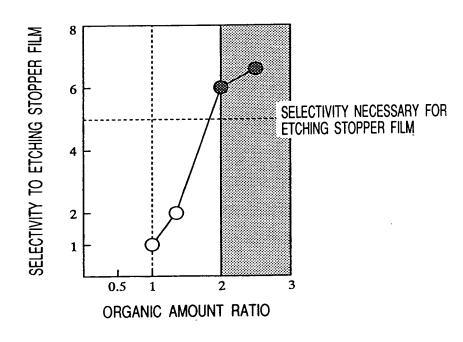
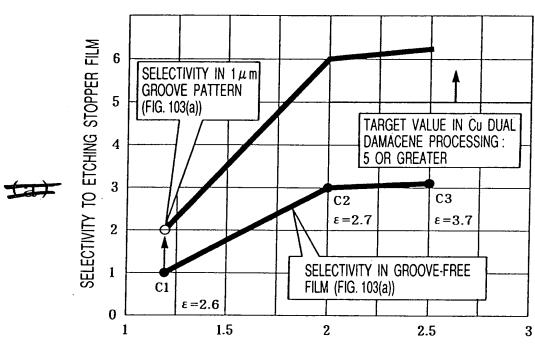


FIG. 104(a)



ORGANIC AMOUNT RATIO (SUPPOSING THAT THE ORGANIC INSULATIG FILM (USED AS AN INTERLEVEL INSULATING FILM) IS 1=20%)

F16.104(b)

STRUCTURE OF C1 STRUCTURE OF C2, c3

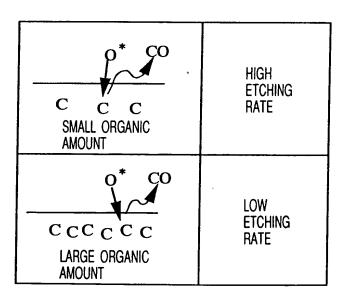
$$\begin{array}{cccc}
CH_3 & CH_3 \\
+ Si-O & - Si-$$

FIG. 108(a)

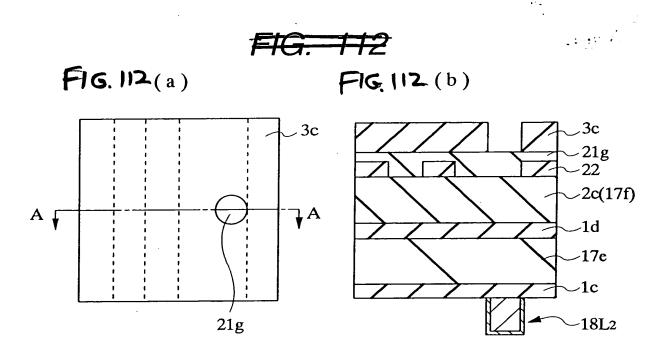


ORGANIC AMOUNT	CF CONSUM- PTION RATE	AMOUNT OF CF DEPOSITS	ETCHING RATE
SMALL (LARGE SiO CONTENT)	HIGH	DEPOSITS: SMALL	HIGH
LARGE (SMALL SiO CONTENT)	LOW	DEPOSITS : LARGE	LOW

(1)



F16.108(b)



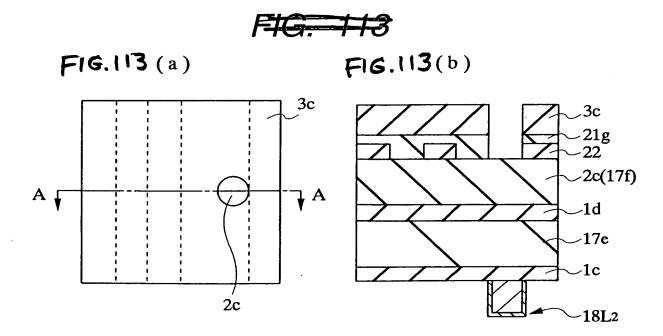
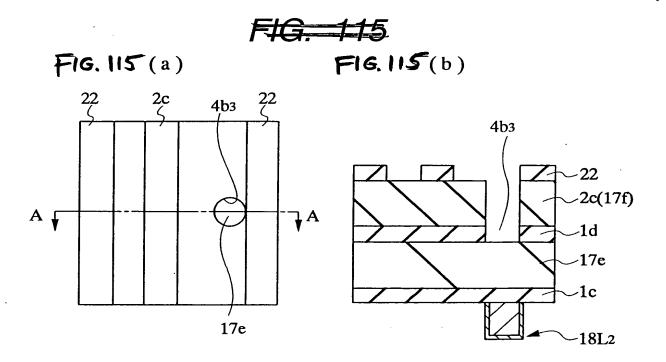


FIG. 114 (a) FIG. 114 (b) 4b3 3c 21g 22c(17f) 17e 18L2



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